

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSVI)

2SK3767

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 3.3\ \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 1.6S$ (typ.)
- Low leakage current: $I_{DSS} = 100\ \mu A$ ($V_{DS} = 600\ V$)
- Enhancement mode: $V_{th} = 2.0$ to $4.0\ V$ ($V_{DS} = 10\ V$, $I_D = 1\ mA$)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Drain-gate voltage ($R_{GS} = 20\ k\Omega$)	V_{DGR}	600	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	2
	Pulse (Note 1)	I_{DP}	5
Drain power dissipation ($T_c = 25^\circ C$)	P_D	25	W
Single pulse avalanche energy (Note 2)	E_{AS}	93	mJ
Avalanche current	I_{AR}	2	A
Repetitive avalanche energy (Note 3)	E_{AR}	4	mJ
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	5.0	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

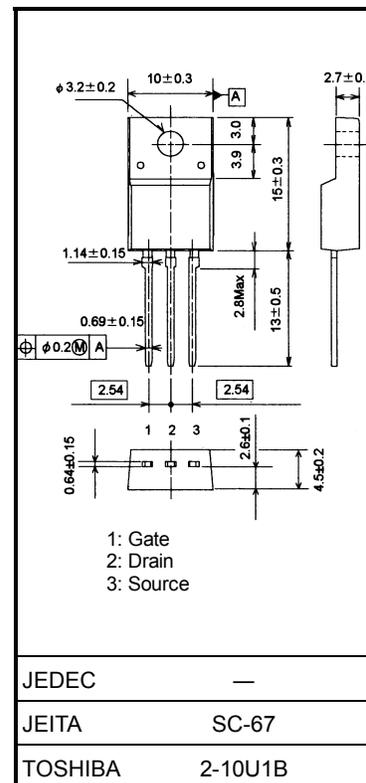
Note 1: Ensure that the channel temperature does not exceed $150^\circ C$.

Note 2: $V_{DD} = 90\ V$, $T_{ch} = 25^\circ C$ (initial), $L = 41\ mH$, $R_G = 25\ \Omega$, $I_{AR} = 2\ A$

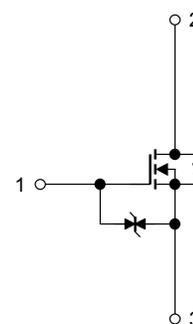
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

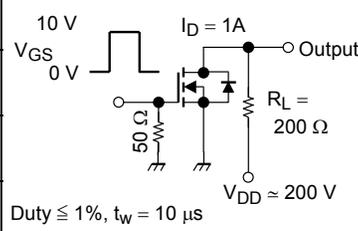
Unit: mm



Weight : 1.7 g (typ.)



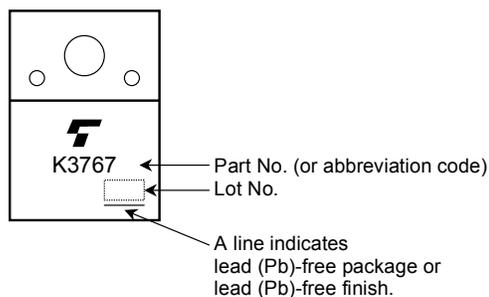
Electrical Characteristics (Ta = 25°C)

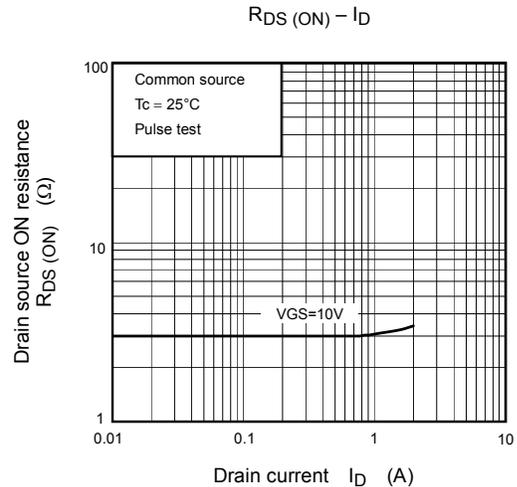
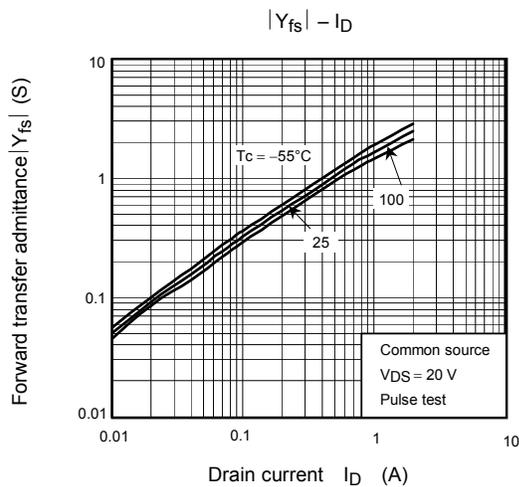
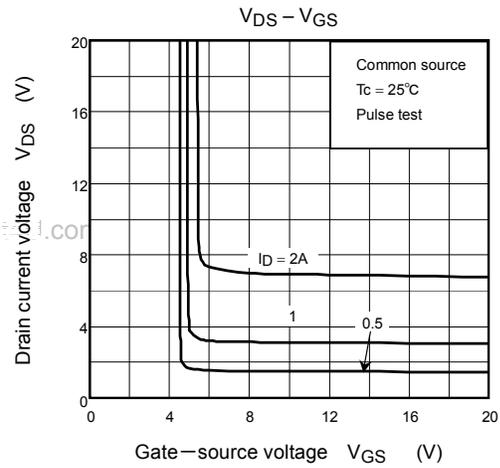
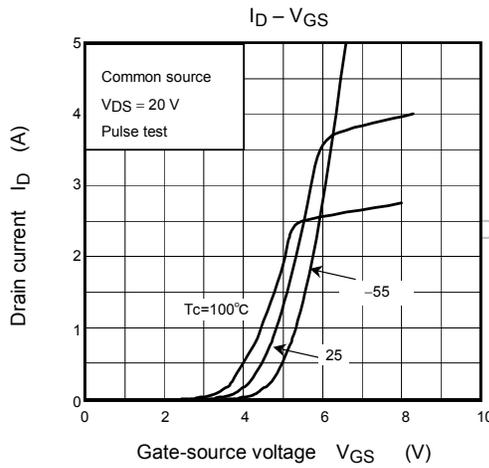
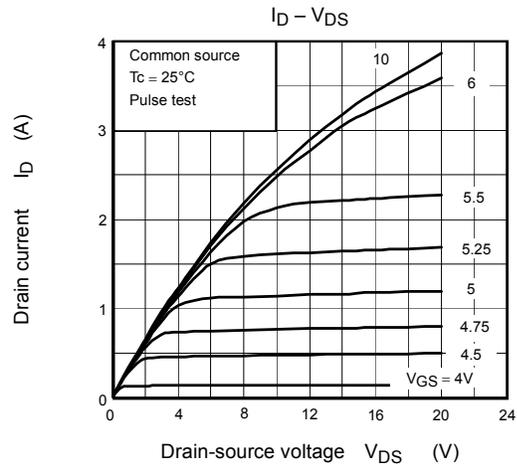
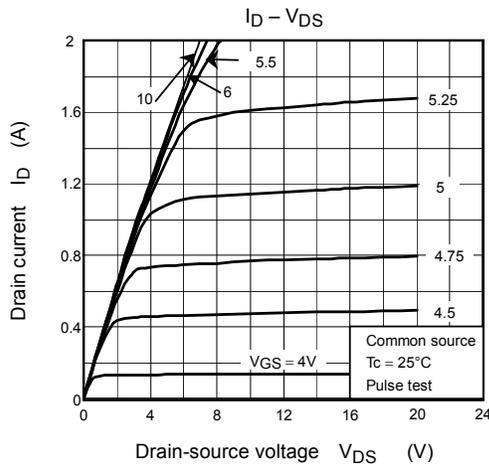
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cut-off current		I_{DSS}	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$	—	3.3	4.5	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	0.8	1.6	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	320	—	pF
Reverse transfer capacitance		C_{rss}		—	30	—	
Output capacitance		C_{oss}		—	100	—	
Switching time	Rise time	t_r		—	15	—	ns
	Turn-on time	t_{on}		—	55	—	
	Fall time	t_f		—	20	—	
	Turn-off time	t_{off}		Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$	—	80	
Total gate charge		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$	—	9	—	nC
Gate-source charge		Q_{gs}		—	5	—	
Gate-drain charge		Q_{gd}		—	4	—	

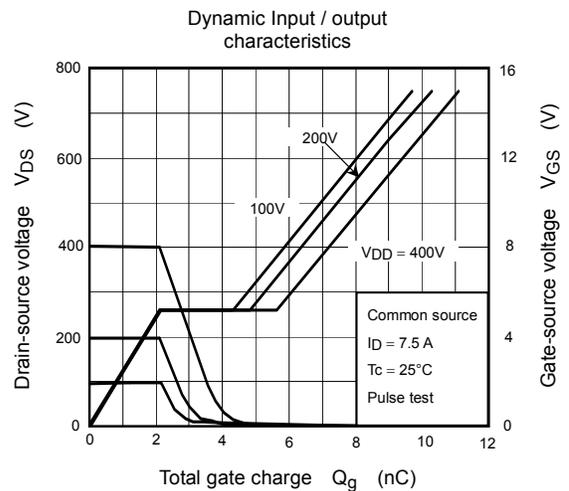
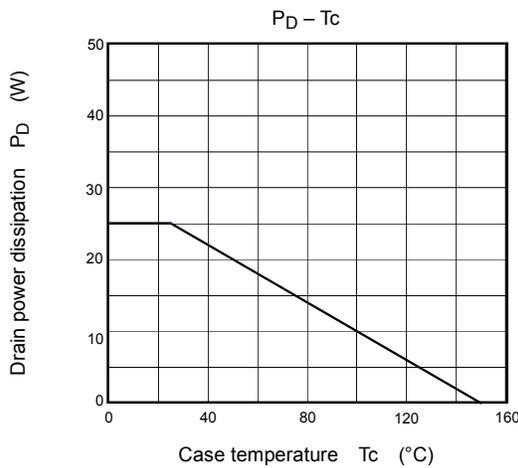
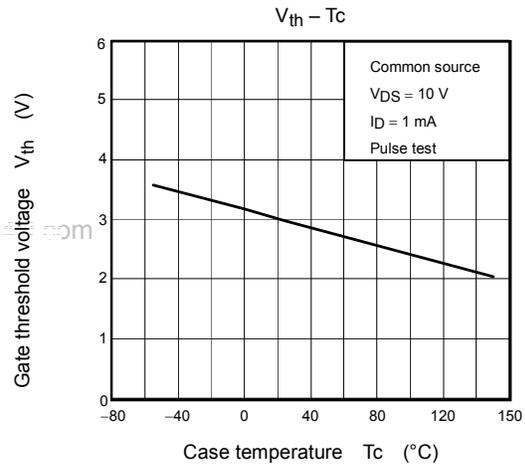
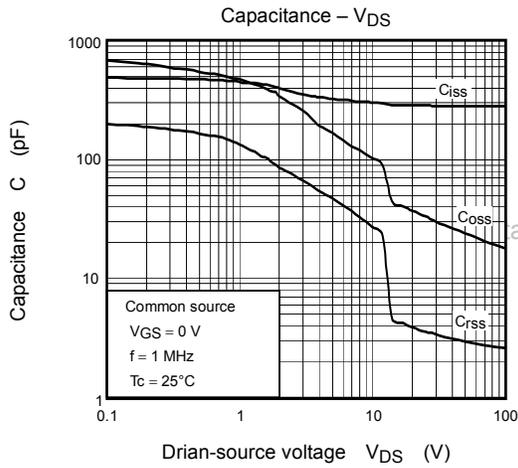
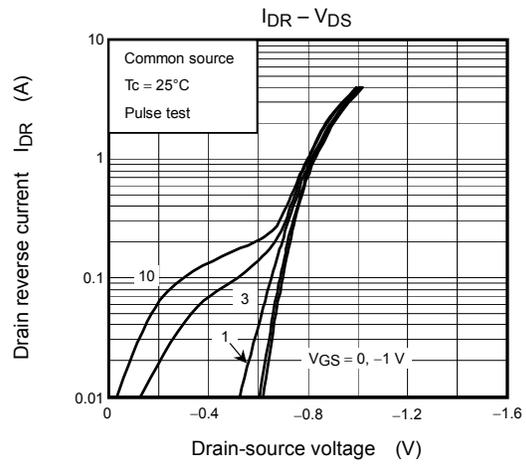
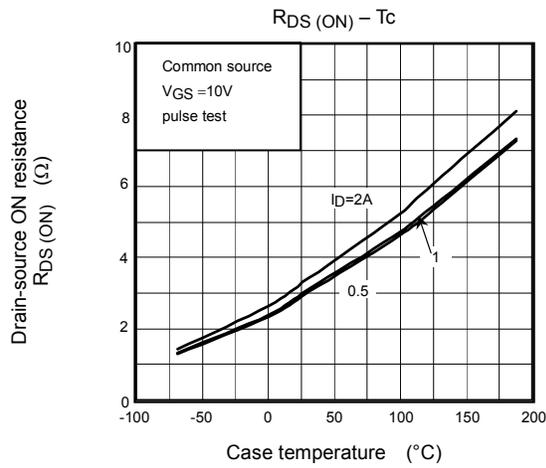
Source-Drain Ratings and Characteristics (Ta = 25°C)

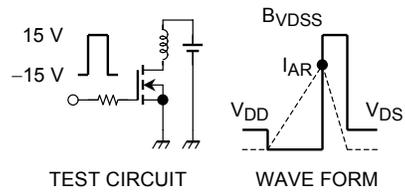
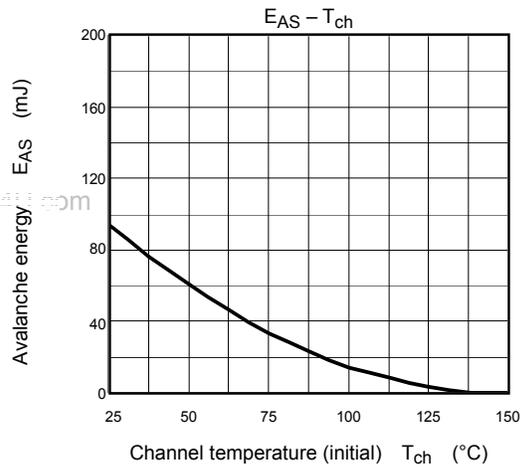
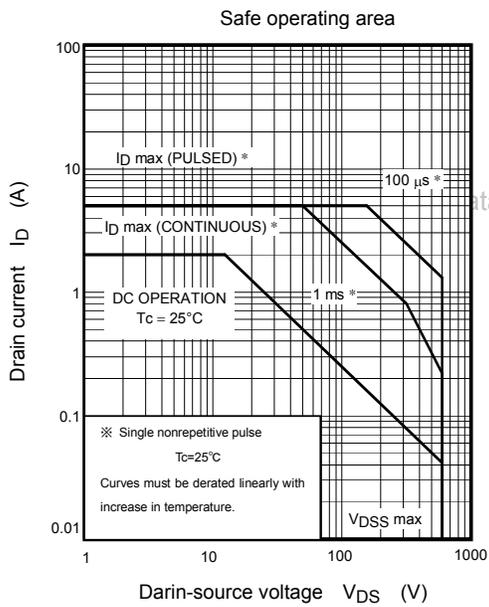
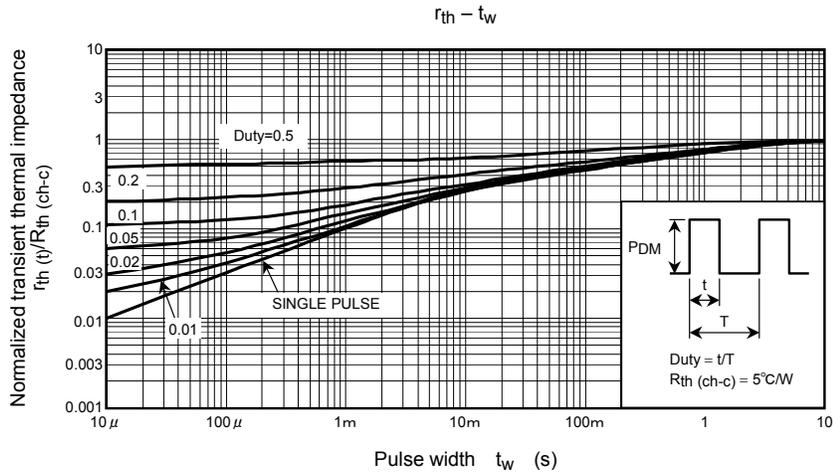
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	2	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	5	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 2 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 2 \text{ A}, V_{GS} = 0 \text{ V},$	—	1000	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	3.5	—	μC

Marking









$R_G = 25 \Omega$
 $V_{DD} = 90 \text{ V}, L = 41 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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